Preliminary

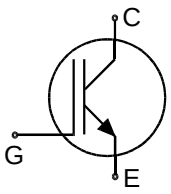
SIGC81T120R2CS

IGBT Chip in NPT-technology

FEATURES:
- 1200V NPT technology 175µm chip
- low turn-off losses
- short tail current
- positive temperature coefficient
- easy paralleling
- integrated gate resistor

This chip is used for:
- IGBT Modules

Applications:
- drives, SMPS, resonant applications



Chip Type	V_{CE}	I_{Cn}	Die Size	Package	Ordering Code
SIGC81T120R2CS	1200V	50A	9.08 X 8.98 mm^2	sawn on foil	Q67050-A4050-A001

MECHANICAL PARAMETER:

Raster size	9.08 X 8.98	mm^2
Emitter pad size	8 x (2.6 x 1.78)	
Gate pad size	1.46 x 0.8	
Area total / active	81.5 / 63.5	
Thickness	175	µm
Wafer size	150	mm
Flat position	90	grd
Max.possible chips per wafer	167 pcs	
Passivation frontside	Photoimide	
Emitter metallization	3200 nm Al Si 1%	
Collector metallization	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	electrically conductive glue or solder	
Wire bond	Al, <500µm	
Reject Ink Dot Size	∅ 0.65mm ; max 1.2mm	
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month	

Edited by INFINEON Technologies AI PS DD HV3, L 7161-T, Edition 1, 24.01.02

Preliminary

SIGC81T120R2CS

MAXIMUM RATINGS:

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	1200	V
DC collector current, limited by T_{jmax}	I_C	50	A
Pulsed collector current, t_p limited by T_{jmax}	I_{cpuls}	100	A
Gate emitter voltage	V_{GE}	±20	V
Operating junction and storage temperature	T_j, T_{stg}	-55 ... +150	°C

STATIC CHARACTERISTICS (tested on chip), T_j=25 °C, unless otherwise specified:

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-emitter breakdown voltage	$V_{(BR)CES}$	V_{GE}=0V , I_C=3mA	1200			V
Collector-emitter saturation voltage	$V_{CE(sat)}$	V_{GE}=15V, I_C=50A	2.7	3.2	3.7	
Gate-emitter threshold voltage	$V_{GE(th)}$	I_C=2mA , V_{GE}=V_{CE}	4.5	5.5	6.5	
Zero gate voltage collector current	I_{CES}	V_{CE}=1200V , V_{GE}=0V			300	µA
Gate-emitter leakage current	I_{GES}	V_{CE}=0V , V_{GE}=30V			300	nA
Integrated gate resistor	R_{Gint}			5	7	Ω

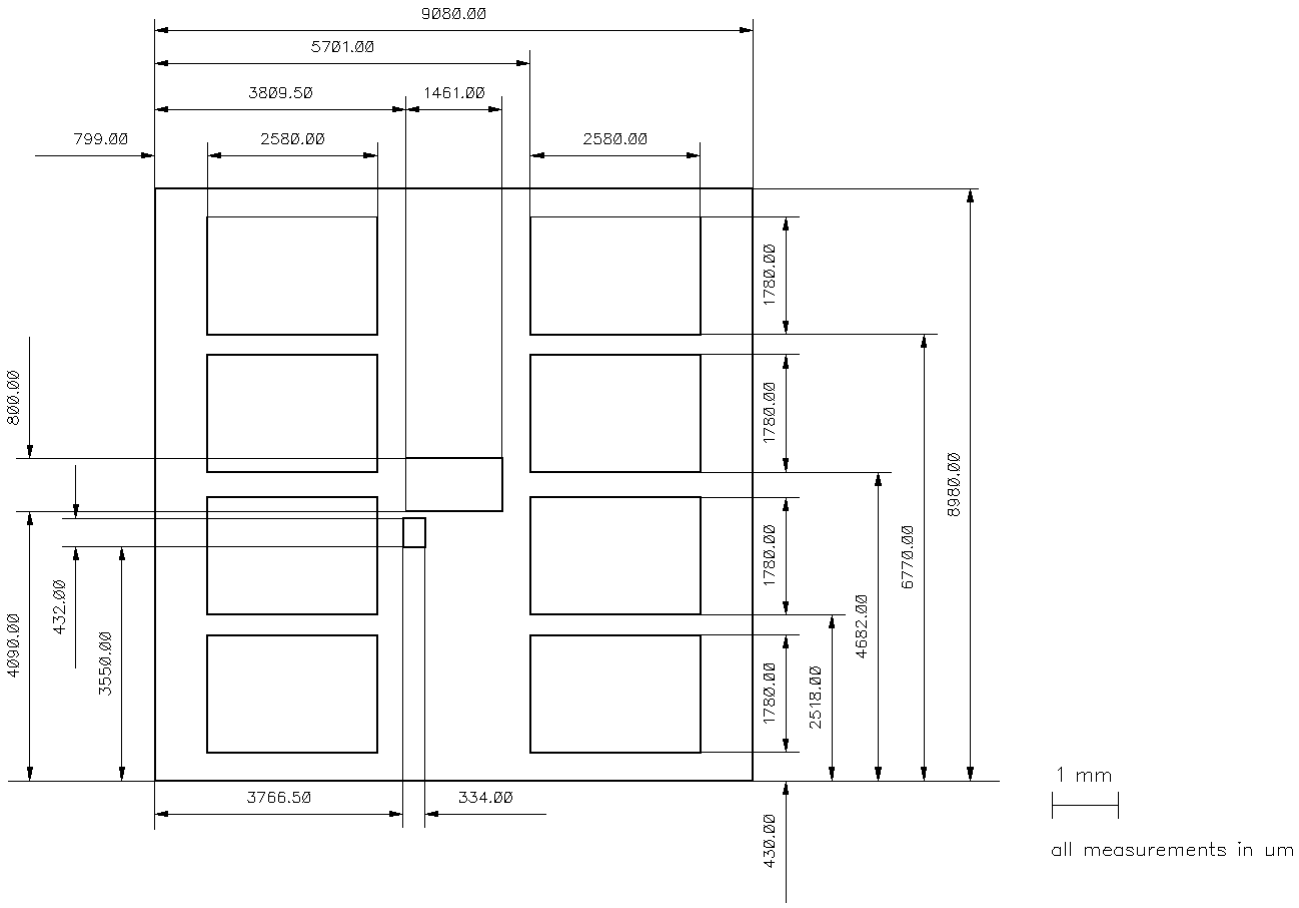
ELECTRICAL CHARACTERISTICS (tested at component):

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	C_{iss}	V_{CE}=25V,	-	3.3		nF
Output capacitance	C_{oss}	V_{GE}=0V,	-	0.5		
Reverse transfer capacitance	C_{rss}	f=1MHz	-	0.22		

SWITCHING CHARACTERISTICS (tested at component), Inductive Load

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Turn-on delay time	$t_{d(on)}$	T_j=125°C	-	tbd		ns
Rise time	t_r	V_{CC}=600V,	-	tbd		
Turn-off delay time	$t_{d(off)}$	I_C=50A, V_{GE}=-15/15V,	-	tbd		
Fall time	t_f	R_G= xxΩ	-	tbd		

CHIP DRAWING:



Preliminary

SIGC81T120R2CS

FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the device data sheet		tbd

DESCRIPTION:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

Published by
Infineon Technologies AG i Gr.,
Bereich Kommunikation
St.-Martin-Strasse 53,
D-81541 München

Attention please!

The information herein is given to describe certain components and shall not be considered as warranted characteristics.

Terms of delivery and rights to technical change reserved.

We hereby disclaim any and all warranties, including but not limited to warranties of non-infringement, regarding circuits, descriptions and charts stated herein.

Infineon Technologies is an approved CECC manufacturer.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office in Germany or our Infineon Technologies Representatives world-wide (see address list).

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and / or maintain and sustain and / or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.